

FIG. 1

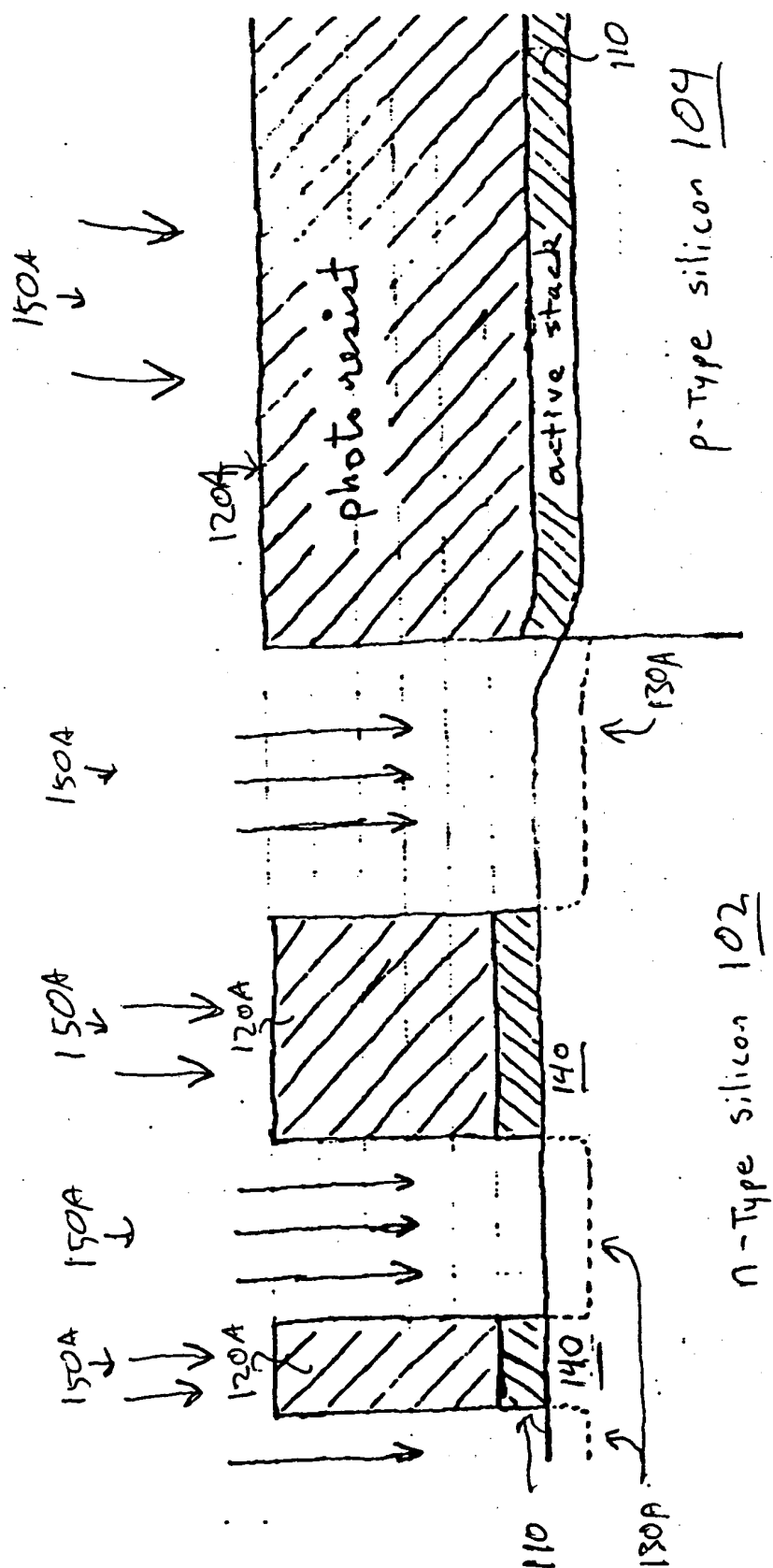


Fig. 1

Hand-drawn cross-sectional diagram of a semiconductor device. The diagram shows a central region labeled "photoresist 120B" with a thickness of 140. This central region is flanked by two side regions, each labeled "130A" and having a thickness of 150B. The entire structure is on a substrate labeled "P-type silicon 104" with a thickness of 130B. Arrows indicate the direction of light or etching from the top. The photoresist layer is shown with a hatched pattern, and the substrate is shown with a solid pattern.

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